

KSA3010 PNP Epitaxial Silicon Transistor

Audio Power Amplifier

- High Current Capability : I_C = 6A
- High Power Dissipation
- · Wide S.O.A
- · Complement to KSC4010



January 2007

1.Base 2.Collector 3.Emitter

Absolute Maximum Ratings* Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-120	V
V _{CEO}	Collector-Emitter Voltage	-120	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current (DC)	-6	А
I _{CP}	Collector Current (Pulse)	-12	А
P _C	Collector Dissipation (T _C =25°C)	60	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 50 ~ 150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150°C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
R _{0JC} Thermal Resistance, Junction to Case		2.0	°C/W

Device mounted on the minimum pad size

Electrical Characteristics* T_a = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = -5A, I _B = 0	-120	-	-	V
I _{CBO}	Collector Cut-off Current	V _{CB} = -120V, I _E = 0	-	-	-10	μA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$	-	-	-10	μA
h _{FE}	DC Current Gain	V_{CE} = -5V, I_{C} = -1A,	55	-	160	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = -5A, I _B = -0.5A	-	-	-2.5	V
V _{BE} (on)	Base-Emitter ON Voltage	V_{CE} = -5V, I_{C} = -5A	-	-	-1.5	V
f _T	Current Gain Bandwidth Product	V _{CE} = -5V, I _C = -1A	-	30	-	MHz
C _{ob}	Output Capacitance	V _{CB} =-10V, I _E =0, f=1MHz	-	180	-	pF

Pulse Test: Pulse Width $\leq 300 \mu s,$ Duty Cycle $\leq 2.0\%$

h_{FF} Classification

Classification	R	0
h _{FE}	55 ~ 110	80 ~ 160

Package Marking and Ordering Information

Device Item (note)	Device Marking	Package	Packing Method	Qty(pcs)
KSA3010RTU	A3010R	TO-3P	TUBE	450
KSA3010OTU	A3010O	TO-3P	TUBE	450

Note : The Suffix "-TU" means the Tube packing method, which can be on fairchildsemi website at http://www.fairchildsemi.com/packaging

Typical Characteristics 10 10 200 180mA ¢ 140mA Ic(A), COLLECTOR CRRENT -120n hFE, DC CURRENT GAIN -100mA Tc=100% I_B=-80mA 6 -60m/ 5 10 -40mA 3 2 0 L 0 10¹ L 0.1 9 6 2 5 10 3 4 8 V_{CE}(V), COLLECTOR EMITTER VOLTAGE I_C(A), COLLECTOR CURRENT Figure 1. Static Characteristic Figure 2. DC current Gain 10 =101 V_{CE}(sat), SATURATION VOLTAGE Ic(A), COLLECTOR CURRENT -5V V_{CE}= 7 6 5 T_=100°C 0.1 =100=25 2 0.01 L 0.01 0 ∟ 0.2 0.1 10 0.4 0.8 1.0 1.2 0.6 1.4 I_C(A), COLLECTOR CURRENT V_{BE}(V), BASE EMITTER VOLTAGE Figure 3. Collector-Emitter Saturation Voltage Figure 4. Base-Emitter On Voltage -100 100 90 Ic MAX. (Pulse) P_G(W), POWER DISSIPATION 80 Ic[A], COLLECTOR CURRENT -10 70 Ic MAX. (DC) 60 50 -40 30 -0. 20 MAX *SINGLE NONREPETITIVE 10 ß PULSE T_c=25[°C] -0.01 └ 0.1 0 L

Figure 6. Power Derating

T_c(℃), CASE TEMPERATURE

75

50

100

125

150

175

25

10

V_{CE}[V], COLLECTOR-EMITTER VOLTAGE

Figure 5. Safe Operating Area





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